

ABSTRACT OF THE DISCLOSURE

Disclosed is a semiconductor device comprising  
a semiconductor substrate, a capacitor structure formed  
above the semiconductor substrate and comprising  
5 a first electrode, a second electrode provided below  
the first electrode, a third electrode provided below  
the second electrode, a first dielectric film provided  
between the first electrode and the second electrode,  
and a second dielectric film provided between the  
10 second electrode and the third electrode, an insulating  
film covering the capacitor structure and having  
a first hole reaching the first electrode, a second  
hole reaching the second electrode, and a third hole  
reaching the third electrode, a first conductive  
15 connection electrically connecting the first electrode  
and the third electrode and having portions buried in  
the first and third holes, and a second conductive  
connection formed separately from the first conductive  
connection and having a portion buried in the second  
20 hole.